

PROCESS CP285

Power Transistor

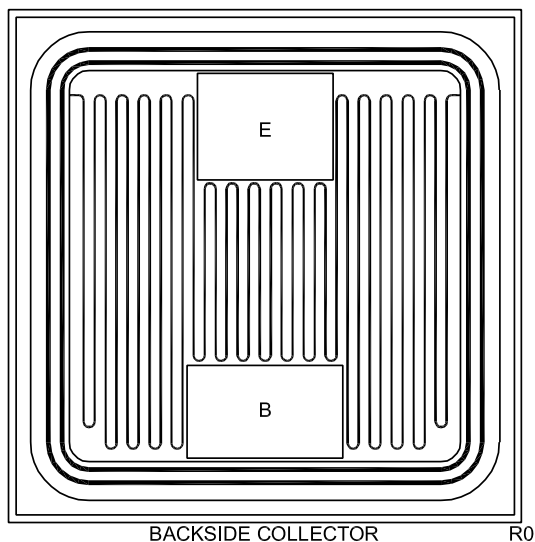
[查询"CP285"供应商](#) Silicon Power Transistor Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

Die Size	105 x 105 MILS
Die Thickness	9.5 MILS
Base Bonding Pad Area	32 x 22 MILS
Emitter Bonding Pad Area	33 x 24 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Ti/Ni/Ag - (3000Å, 10,000Å, 10,000Å)

GEOMETRY



GROSS DIE PER 5 INCH WAFER

1,486

PRINCIPAL DEVICE TYPES

MJE13005

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